Microelectronics II midterm exam

姓名	:	
學號	:	

date: 2013/04/24

注意事項:1. 題目卷、答案卷,皆要填寫考生姓名與學號;

2. 考試完畢,請將題目卷、答案卷一倂繳回,未繳回者,不予計分;

- 1. (22%) Fig. 1 is a MOS cascode amplifier. Assume that two transistors, Q_1 and Q_2 , have the same g_m and r_o .
 - (1) Find A_{v1} , A_{v2} , R_{in2} and R_o , where $A_{v1} = v_{o1}/v_i$ and $A_{v2} = v_o/v_{o1}$. (12%)
 - (2) If $R_L = 2r_o$, find A_{v1} and R_{in2} . (6%)
 - (3) Explain how to select R_L so that A_{v1} can be comparable with the intrinsic gain of Q_1 (in the same order of magnitude). (4%)

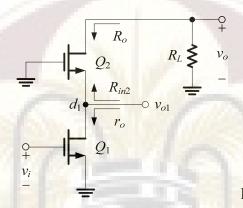


Fig. 1

(Solution)

(1) Find A_{v1} , A_{v2} , R_{in2} and R_o , where $A_{v1} = v_{o1}/v_i$ and $A_{v2} = v_o/v_{o1}$. (12%)

Answer:

$$A_{v} = A_{v1}A_{v2} = -g_{m1}(g_{m2}r_{o2}r_{o1} // R_{L}) = -g_{m1}(g_{m2}r_{o2}r_{o} // R_{L}), where: r_{o} = r_{o1}$$

$$A_{v1} = \frac{v_{o1}}{v_{i}} = -g_{m1}(r_{o1} // R_{in2}) = -g_{m1}(r_{o} // R_{in2})$$

$$A_{v2} = \frac{A_{v}}{A_{v1}} = \frac{g_{m2}r_{o2}r_{o1} //R_{L}}{r_{o1} //R_{in2}} = \frac{g_{m2}r_{o2}r_{o1} //R_{L}}{r_{o1} //\left(\frac{R_{L} + r_{o2}}{1 + g_{m2}r_{o2}}\right)} = \frac{\frac{1}{r_{o1}} + \frac{1 + g_{m2}r_{o2}}{R_{L} + r_{o2}}}{\frac{1}{g_{m2}r_{o2}r_{o1}} + \frac{1}{R_{L}}} = \frac{\frac{(R_{L} + r_{o2}) + (1 + g_{m2}r_{o2})r_{o1}}{r_{o1}(R_{L} + r_{o2})}}{\frac{R_{L} + g_{m2}r_{o2}r_{o1}}{R_{L}}} = \frac{\frac{R_{L} + r_{o2}}{R_{L} + r_{o2}} + \frac{(R_{L} + r_{o2}) + (1 + g_{m2}r_{o2})r_{o1}}{g_{m2}r_{o2}r_{o1}R_{L}}}{\frac{R_{L} + g_{m2}r_{o2}r_{o1}}{R_{L} + r_{o2}}} = \frac{(R_{L} + r_{o2}) + (1 + g_{m2}r_{o2})r_{o1}}{R_{L} + r_{o2}} \frac{g_{m2}r_{o2}R_{L}}{R_{L} + g_{m2}r_{o2}r_{o1}}|_{\therefore g_{m2}r_{o2}r_{o1}}}{R_{L} + g_{m2}r_{o2}r_{o1}}|_{\therefore g_{m2}r_{o2}r_{o1}}$$

$$\rightarrow A_{v2} = \frac{\left(R_L + r_{o2}\right) + \left(1 + g_{m2}r_{o2}\right)r_{o1}}{r_{o1}\left(R_L + r_{o2}\right)} \frac{g_{m2}r_{o2}r_{o1}R_L}{R_L + g_{m2}r_{o2}r_{o1}} = \frac{\left(R_L + r_{o2}\right) + \left(1 + g_{m2}r_{o2}\right)r_{o1}}{R_L + r_{o2}} \frac{g_{m2}r_{o2}R_L}{R_L + g_{m2}r_{o2}r_{o1}} \Big|_{\therefore g_{m2}r_{o2}r_{o1} > r_{o1}}$$

$$\rightarrow A_{v2} \approx \frac{R_L + r_{o2} + g_{m2} r_{o2} r_{o1}}{R_L + r_{o2}} \frac{g_{m2} r_{o2} R_L}{R_L + g_{m2} r_{o2} r_{o1}} \bigg|_{g_{m2} r_{o2} r_{o1} >> r_{o2}} \approx \frac{R_L + g_{m2} r_{o2} r_{o1}}{R_L + r_{o2}} \frac{g_{m2} r_{o2} R_L}{R_L + g_{m2} r_{o2} r_{o1}} = \frac{g_{m2} r_{o2} R_L}{R_L + r_{o2}}$$

$$\rightarrow A_{v2} = g_{m2} \left(r_{o2} // R_L \right)$$

$$R_{in2} = \frac{R_L + r_{o2}}{1 + g_{m2} r_{o2}}$$

$$R_o = r_{o2} + (1 + g_{m2}r_{o2})r_{o1} \approx g_{m2}r_{o2}r_{o1} = g_{m2}r_{o2}r_{o}$$

(2) If $R_L = 2r_o$, find A_{v1} and R_{in2} . (6%) *Answer*:

$$A_{v1} = \frac{v_{o1}}{v_i} = -g_{m1} \left(r_o // R_{in2} \right) = -g_{m1} \frac{r_o R_{in2}}{r_o + R_{in2}} = -g_{m1} \frac{r_o \frac{3r_o}{1 + g_{m2} r_o}}{r_o + \frac{3r_o}{1 + g_{m2} r_o}} = -g_{m1} \frac{\frac{3r_o}{1 + g_{m2} r_o}}{1 + \frac{3}{1 + g_{m2} r_o}} = -g_{m1} \frac{\frac{3r_o}{1 + g_{m2} r_o}}{1 + \frac{3}{1 + g_{m2} r_o}} = -g_{m1} \frac{\frac{3r_o}{1 + g_{m2} r_o}}{1 + g_{m2} r_o}$$

$$A_{v1} = -g_{m1} \left(\frac{3r_o}{4 + g_{m2} r_o} \right)$$

$$R_{in2} = \frac{R_L + r_{o2}}{1 + g_{m2} r_{o2}} \Big|_{R_L = 2r_o} = \frac{3r_o}{1 + g_{m2} r_o}$$

(3) Explain how to select R_L so that $A_{\nu 1}$ can be comparable with the intrinsic gain of Q_1 (in the same order of magnitude). (4%)

Answer:

$$A_{v1} = \frac{v_{o1}}{v_i} = -g_{m1} \left(r_{o1} // R_{in2} \right) = -g_{m1} \left(r_{o} // R_{in2} \right) = -g_{m1} \left(r_{o} // \frac{R_L + r_{o2}}{1 + g_{m2} r_{o2}} \right) \dots (1)$$

Intrinsic gain of Q_1 ,

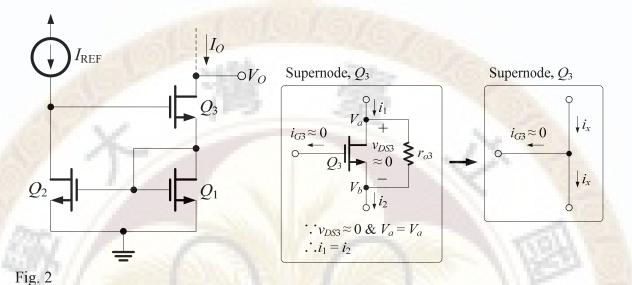
$$A_{v1}' = -g_{m1}(r_o // R_L)....(2)$$

Let
$$(1) = (2)$$
,

$$r_o / \frac{R_L + r_{o2}}{1 + g_{m2} r_{o2}} = r_o / R_L \rightarrow \frac{1}{r_o} + \frac{1 + g_{m2} r_{o2}}{R_L + r_{o2}} = \frac{1}{r_o} + \frac{1}{R_L} \rightarrow \frac{1 + g_{m2} r_{o2}}{R_L + r_{o2}} = \frac{1}{R_L}$$

- 2. Fig. 2 shows a MOS Wilson current source. Assume the transistors have identical parameters.
 - (1) Find the output resistance in terms of g_m and r_o of the transistors. (10%)
 - (2) The V_{DS} of Q_2 is higher than that of Q_1 , which results in difference between I_{REF} and I_O . If $V_{GS3} = V_{GS2} = V_{GS1}$ and $V_A = 20 \ V_{GS1}$, find I_O/I_{REF} . (8%)

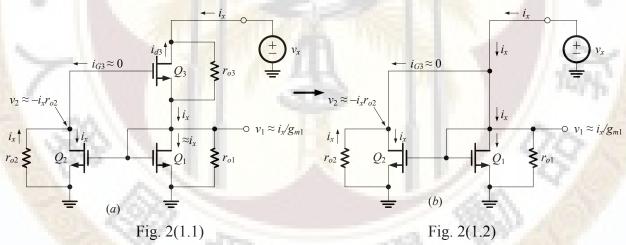
 (Hint: $I_D = (1/2)k_n'(W/L)(V_{GS}-V_t)^2(1+V_{DS}/V_A)$)



(Solution)

(1) Find the output resistance in terms of g_m and r_o of the transistors. (10%)

Answer:



where: the small-signal equivalent circuit of Q_3 is shown in Fig. 2(1.2).

Note: The test takers do not need to plot the circuit shown in Fig. 2(1.1) and Fig. 2(1.2). They are illustrated to help understand the process of finding the answers.

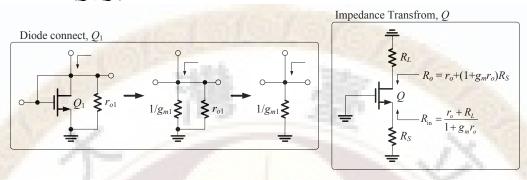
$$i_{d3} = g_{m3}v_{gs3} = g_{m3}\left(v_{g3} - v_{s3}\right) = g_{m3}\left(-i_{x}r_{o2} - \frac{i_{x}}{g_{m1}}\right) = -i_{x}g_{m3}\left(r_{o2} + \frac{1}{g_{m1}}\right) \approx -\left(g_{m3}r_{o2}\right)i_{x}$$

$$v_{x} = -i_{d3}r_{o3} + v_{1} = g_{m3}r_{o2}r_{o3}i_{x} + \frac{i_{x}}{g_{m1}} = \left(g_{m3}r_{o2}r_{o3} + \frac{1}{g_{m1}}\right)i_{x} \approx g_{m3}r_{o2}r_{o3}i_{x}$$

$$R_{o} = \frac{v_{x}}{i_{x}} = \left(g_{m3}r_{o3}\right)r_{o2}$$

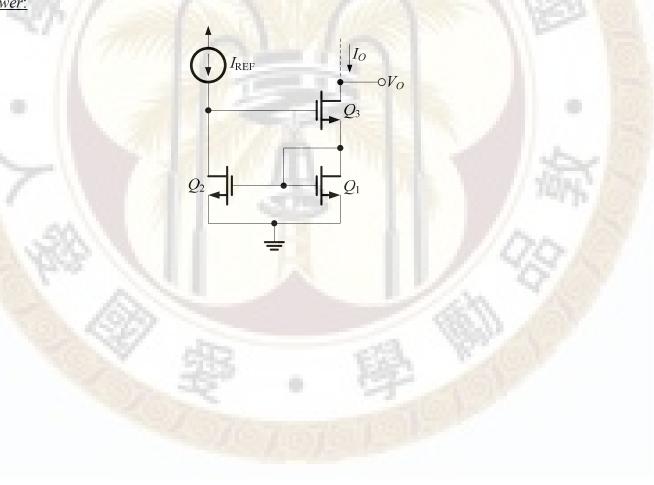
直觀解法:因為 Q_1 為 diode connect 電路,因此,在求該電路之小訊號輸出阻抗為目的時, Q_1 並不會參與阻抗轉換之過程,亦即,從 drain 端看入之阻抗是 source 端看到阻抗之 $(1+g_mr_o)$ 倍。

原因是 Q_1 為 diode connect 電路,在此電路中不具電晶體放大之功能。而真是會參與這樣轉換的電晶體,即只剩 (Q_2,Q_3) 。

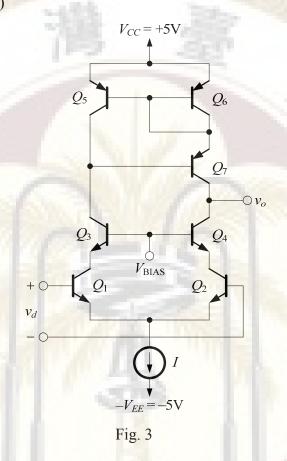


(2) The V_{DS} of Q_2 is higher than that of Q_1 , which results in difference between I_{REF} and I_O . If $V_{GS3} = V_{GS2} = V_{GS1}$ and $V_A = 20 \ V_{GS1}$, find I_O/I_{REF} . (8%) (Hint: $I_D = (1/2)k_n'(W/L)(V_{GS}-V_t)^2(1+V_{DS}/V_A)$)

Answer:



- 3. (27%) Fig. 3 shows a differential cascode amplifier with an active load formed by a Wilson current mirror. Assume all the transistors are identical.
 - (1) Plot the small-signal model of the Wilson current mirror (3%)
 - (2) Find the output resistance of the Wilson current mirror (8%)
 - (3) Plot the small-signal model of the bipolar cascode composed of Q_2 and Q_4 (3%)
 - (4) Find the output resistance of the bipolar cascode composed of Q_2 and Q_4 (8%)
 - (5) Prove that the differential gain of this differential cascode amplifier is given approximately by $A_d = (\beta g_m r_o)/3$ (5%)

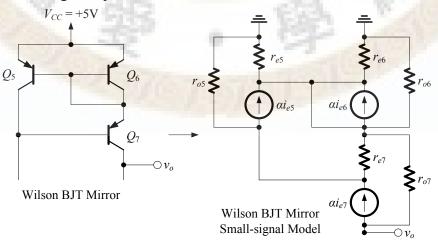


(Solution)

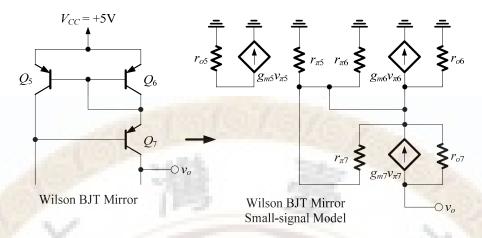
(1) Plot the small-signal model of the Wilson current mirror (3%)

Answer:

(Case 1) T model small-signal equivalent circuits.

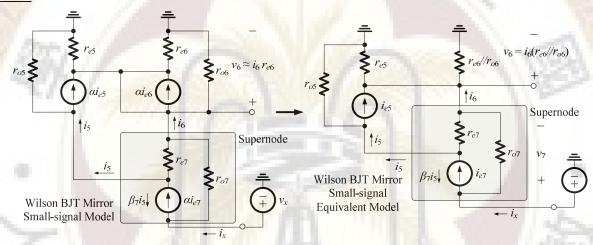


(Case 2) π model small-signal equivalent circuits.



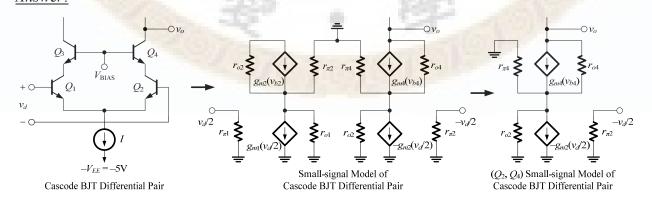
(2) Find the output resistance of the Wilson current mirror (8%)

Answer:

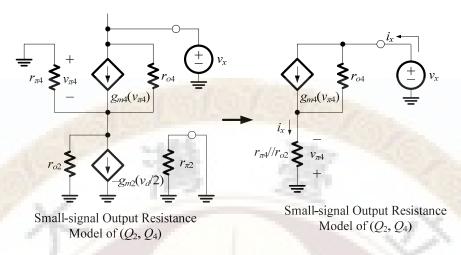


$$\begin{aligned} & v_{7} = \left(\beta_{7}i_{5} + i_{x}\right)r_{o7}, \ v_{6} = i_{6}\left(r_{e6} / / r_{o6}\right) \approx i_{6}r_{e6} \\ & v_{x} = v_{6} + v_{7} = i_{6}r_{e6} + \left(\beta_{7}i_{5} + i_{x}\right)r_{o7} = \frac{i_{x}}{2}r_{e6} + \left(\beta_{7}\frac{i_{x}}{2} + i_{x}\right)r_{o7} = i_{x}\left[\frac{r_{e6}}{2} + \left(\frac{\beta_{7}}{2} + 1\right)r_{o7}\right] \approx i_{x}\frac{\beta_{7}}{2}r_{o7} \\ & R_{o} = R_{o.upper} = \frac{v_{x}}{i_{x}} = \frac{\beta_{7}}{2}r_{o7}, \ \ where : i_{6} \approx i_{5} = \frac{i_{x}}{2} \end{aligned}$$

(3) Plot the small-signal model of the bipolar cascode composed of Q_2 and Q_4 (3%) *Answer*:



(4) Find the output resistance of the bipolar cascode composed of Q_2 and Q_4 (8%) *Answer*:

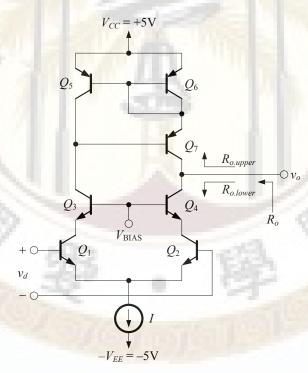


$$v_{x} = (i_{x} - g_{m4}v_{\pi4})r_{o4} + i_{x}(r_{\pi4} // r_{o2}) = i_{x}[1 + g_{m4}(r_{\pi4} // r_{o2})]r_{o4} + i_{x}(r_{\pi4} // r_{o2})$$
where: $-v_{\pi4} = i_{x}(r_{\pi4} // r_{o2})$

$$R_{o} = R_{o.lower} = \frac{v_{x}}{i_{x}} = \left[1 + g_{m4} \left(r_{\pi 4} // r_{o2}\right)\right] r_{o4} + \left(r_{\pi 4} // r_{o2}\right) \approx g_{m4} \left(r_{\pi 4} // r_{o2}\right) r_{o4} \approx g_{m4} r_{\pi 4} r_{o4} = \beta_{4} r_{o4} r_{o4} + \beta_{4} r_{o4} r_{o4} r_{o4} + \beta_{4} r_{o4} r_$$

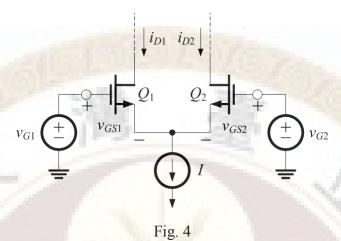
(5) Prove that the differential gain of this differential cascode amplifier is given approximately by $A_d = (\beta g_m r_o)/3$ (5%)

Answer:



$$\begin{split} R_{o.upper} &= \frac{\beta_7}{2} r_{o7}, \ R_{o.lower} = \beta_4 r_{o4} \rightarrow R_o = R_{o.upper} \ // \ R_{o.lower} = \left(\frac{1}{2} \beta r_o\right) \! // \ \beta r_o = \frac{1}{3} \beta r_o \\ A_d &= G_m R_o = \frac{1}{3} \left(\beta g_m r_o\right) \end{split}$$

- 4. (13%) Fig. 4 shows a MOS differential amplifier. Assume Q_1 and Q_2 are in saturation.
 - (1) Find the currents i_{D1} and i_{D2} in terms of $v_d \equiv v_{G1} v_{G2}$ and other semiconductor parameters (8%)
 - (2) When the tail current I is steered entirely into Q_1 . Find v_d in this case. (5%)



(Solution)

(1) Find the currents i_{D1} and i_{D2} in terms of $v_d \equiv v_{G1} - v_{G2}$ and other semiconductor parameters (8%) Answer:

$$\begin{cases}
i_{D1} = \frac{1}{2}k'_{n}\frac{W}{L}(v_{GS1} - V_{t})^{2} \\
i_{D2} = \frac{1}{2}k'_{n}\frac{W}{L}(v_{GS2} - V_{t})^{2}
\end{cases} \Rightarrow \begin{cases}
\sqrt{i_{D1}} = \sqrt{\frac{1}{2}k'_{n}\frac{W}{L}}(v_{GS1} - V_{t}).....(1) \\
\sqrt{i_{D2}} = \sqrt{\frac{1}{2}k'_{n}\frac{W}{L}}(v_{GS2} - V_{t}).....(2)
\end{cases}$$

$$v_{d} = v_{GS1} - v_{GS2} = v_{G1} - v_{G2}$$

$$(1) - (2), \Rightarrow \sqrt{i_{D1}} - \sqrt{i_{D2}} = \sqrt{\frac{1}{2}k'_{n}\frac{W}{L}}v_{d}......(3)$$

$$(3)^{2} \Rightarrow (\sqrt{i_{D1}} - \sqrt{i_{D2}})^{2} = \frac{1}{2}k'_{n}\frac{W}{L}v_{d}^{2} \Rightarrow i_{D1} + i_{D2} - 2\sqrt{i_{D1}}\sqrt{i_{D2}} = \frac{1}{2}k'_{n}\frac{W}{L}v_{d}^{2}$$

$$\Rightarrow 2\sqrt{i_{D1}}i_{D2} = I - \frac{1}{2}k'_{n}\frac{W}{L}v_{d}^{2}......(4), \quad where: i_{D1} + i_{D2} = I......(5)$$

(b)
$$\left(\sqrt{i_{D1}} + \sqrt{i_{D2}}\right)^2 = i_{D1} + i_{D2} + 2\sqrt{i_{D1}i_{D2}} = 2I - \frac{1}{2}k_n'\frac{W}{L}v_d^2 \rightarrow \sqrt{i_{D1}} + \sqrt{i_{D2}} = \sqrt{2I - \frac{1}{2}k_n'\frac{W}{L}v_d^2} \dots (6)$$

$$(c) \quad (3) + (6) \to 2\sqrt{i_{D1}} = \sqrt{\frac{1}{2}k_{n}'} \frac{W}{L} v_{d} + \sqrt{2I - \frac{1}{2}k_{n}'} \frac{W}{L} v_{d}^{2}} \to i_{D1} = \frac{1}{4} \left(\sqrt{\frac{1}{2}k_{n}'} \frac{W}{L} v_{d} + \sqrt{2I - \frac{1}{2}k_{n}'} \frac{W}{L} v_{d}^{2}} \right)^{2}$$

$$\to i_{D1} = \frac{1}{4} \left(\frac{1}{2}k_{n}' \frac{W}{L} v_{d}^{2} + 2I - \frac{1}{2}k_{n}' \frac{W}{L} v_{d}^{2} + 2\sqrt{\frac{1}{2}k_{n}'} \frac{W}{L} v_{d} \sqrt{2I - \frac{1}{2}k_{n}'} \frac{W}{L} v_{d}^{2}} \right)$$

$$= \frac{I}{2} + \sqrt{\frac{1}{2}k_{n}'} \frac{W}{L} \left(\frac{v_{d}}{2} \right) \sqrt{2I - \frac{1}{2}k_{n}'} \frac{W}{L} v_{d}^{2}} = \frac{I}{2} + \sqrt{\frac{1}{2}k_{n}'} \frac{W}{L} \left(\frac{v_{d}}{2} \right) \sqrt{2I - \frac{1}{2}k_{n}'} \frac{W}{L} v_{d}^{2}}$$

$$= \frac{I}{2} + \sqrt{k_{n}'} \frac{W}{L} I \left(\frac{v_{d}}{2} \right) \sqrt{1 - \frac{1}{I}k_{n}'} \frac{W}{L} \left(\frac{v_{d}}{2} \right)^{2}} = \frac{I}{2} + \sqrt{k_{n}'} \frac{W}{L} I \left(\frac{v_{d}}{2} \right) \sqrt{1 - \frac{(v_{d}/2)^{2}}{I/(k_{n}'} (W/L))}}$$

$$\rightarrow i_{D1} = \frac{I}{2} + \sqrt{k_n' \frac{W}{L} I} \left(\frac{v_d}{2} \right) \sqrt{1 - \frac{(v_d/2)^2}{I/(k_n'(W/L))}}$$

$$(d) \quad \because i_{D1} + i_{D2} = I$$

$$\rightarrow i_{D2} = I - i_{D1} = \frac{I}{2} - \sqrt{k_n' \frac{W}{L} I} \left(\frac{v_d}{2}\right) \sqrt{1 - \frac{(v_d/2)^2}{I/(k_n'(W/L))}}$$

(e) At the bias point, $v_d = 0$, leading to

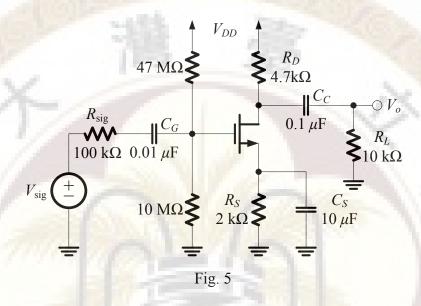
$$(f) \quad i_{D1} = \frac{I}{2} + \sqrt{k_n'} \frac{W}{L} I\left(\frac{v_d}{2}\right) \sqrt{1 - \frac{(v_d/2)^2}{I/(k_n'(W/L))}} = \frac{I}{2} + \left(\frac{I}{V_{OV}}\right) \left(\frac{v_d}{2}\right) \sqrt{1 - \left(\frac{v_d/2}{V_{OV}}\right)^2}$$

$$i_{D2} = \frac{I}{2} - \left(\frac{I}{V_{OV}}\right) \left(\frac{v_d}{2}\right) \sqrt{1 - \left(\frac{v_d/2}{V_{OV}}\right)^2}$$

(2) When the tail current I is steered entirely into Q_1 . Find v_d in this case. (5%) Answer:

- 5. (20%) The NMOS transistor in the discrete common-source amplifier of Fig. 5 is biased to have $g_m = 1 \, mA/V$. Find
 - $(1) A_{\rm M} (4\%),$
 - $(2) f_{p1} (4\%), f_{p2} (4\%),$
 - $(3) f_{p3} (4\%)$ and $f_L (4\%)$

in unit of Hz using the short circuit time-constant method (i.e., the low-frequency 3dB frequency is given by the summation of all poles). Do not forget the (2π) .



(Solution)

 $(1) A_{\rm M} (4\%),$

$$R_G = 47M\Omega // 10M\Omega = 8.25M\Omega \rightarrow (+1\%)$$

$$R_G = 47M\Omega // 10M\Omega = 8.25M\Omega \rightarrow (+1\%)$$

$$R_G = 47M\Omega // 10M\Omega = 8.25M\Omega \rightarrow (+1\%)$$

$$A_{M} = -\frac{R_{G}}{R_{G} + R_{\text{sig}}} g_{m} (R_{D} // R_{L}) \rightarrow (+2\%) = -\frac{8.25 M \Omega}{8.25 M \Omega + 0.1 M \Omega} (1 mA/V) (4.7 k \Omega // 10 k \Omega)$$

$$\rightarrow A_M = -3.16(V/V) \rightarrow (+1\%)$$

 $(2) f_{p1} (4\%), f_{p2} (4\%),$

$$\left. f_{p1} \right|_{\text{@Gate Terminal}} = \frac{1}{2\pi C_G \left(R_G + R_{\text{sig}} \right)} \rightarrow \left(+3\% \right) = \frac{1}{2\pi \times 0.01 \mu F \times \left(8.25 M\Omega + 0.1 M\Omega \right)} = 1.9 Hz \rightarrow \left(+1\% \right)$$

$$\left.f_{p2}\right|_{\text{@Source Terminal}} = \frac{1}{2\pi C_S \left(R_S // \frac{1}{g_m}\right)} \rightarrow \left(+3\%\right) = \frac{1}{2\pi \times 10 \mu F \times \left(2k\Omega // 1k\Omega\right)} = 23.87 Hz \rightarrow \left(+1\%\right)$$

 $(3) f_{p3} (4\%)$ and $f_L (4\%)$

$$\begin{aligned} f_{p3}\Big|_{\text{@Drain Terminal}} &= \frac{1}{2\pi C_C \left(R_D + R_L\right)} \rightarrow \left(+3\%\right) = \frac{1}{2\pi \times 0.1 \mu F \times \left(4.7 k\Omega + 10 k\Omega\right)} = 108.27 Hz \rightarrow \left(+1\%\right) \\ f_L &\approx f_{p3} \rightarrow \left(+3\%\right) = 108.27 Hz \rightarrow \left(+1\%\right) \end{aligned}$$